

# HFA1405

Quad, 560MHz, Low Power, Video **Operational Amplifier** 

November 1996

Features

, eatares
Low Supply Current 5.8mA/Op Amp
• High Input Impedance
• Wide -3dB Bandwidth (Ay = +2) 560MHz
Very Fast Slew Rate 1700V/μs
Gain Flatness (to 50MHz)
Differential Gain 0.02%
Differential Phase 0.03 Degrees
All Hostile Crosstalk (5MHz)60dB

## • Pin Compatible Upgrade to HA5025, CLC414, and **CLC415**

## **Applications**

- Flash A/D Drivers
- Professional Video Processing
- Video Digitizing Boards/Systems
- Multimedia Systems
- RGB Preamps
- Medical Imaging
- Hand Held and Miniaturized RF Equipment
- Battery Powered Communications
- · High Speed Oscilloscopes and Analyzers

## Description

The HFA1405 is a quad, high speed, low power current feedback amplifier built with Harris' proprietary complementary bipolar UHF-1 process.

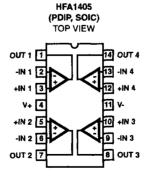
These amplifiers deliver up to 560MHz bandwidth and 1700V/us slew rate, on only 58mW of guiescent power. They are specifically designed to meet the performance, power, and cost requirements of high volume video applications. The excellent gain flatness and differential gain/phase performance make these amplifiers well suited for component or composite video applications. Video performance is maintained even when driving a back terminated cable  $(R_1 = 150\Omega)$ , and degrades only slightly when driving two back terminated cables ( $R_1 = 75\Omega$ ). RGB applications will benefit from the high slew rates, and high full power bandwidth.

The HFA1405 is a pin compatible, low power, high performance upgrade for the popular Harris HA5025, and for the CLC414 and CLC415.

## Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.				
HFA1405IB	-40 to 85	14 Ld SOIC	M14.15				
HFA1405IP	-40 to 85	E14.3					
HA5025EVAL	High Speed Op Amp DIP Evaluation Board						

#### Pinout



## Absolute Maximum Ratings TA = 25°C DC Input Voltage ...... VSUPPLY Output Current (Note 2) . . . . . . . Short Circuit Protected 30mA Continuous 60mA ≤ 50% Duty Cycle ESD Rating

Thormal	Information
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Thermal Resistance (Typical, Note 1)	θ <sub>JA</sub> (°C/W)
SOIC Package	120
PDIP Package	100
Maximum Junction Temperature (Die)	175°C
Maximum Junction Temperature (Plastic Package)	150°C
Maximum Storage Temperature Range65	
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

## **Operating Conditions**

Temperature Range . . . . . . . . . -40°C to 85°C

Human Body Model (Per MIL-STD-883 Method 3015.7) . . . 600V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

- 1.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.
- 2. Output is short circuit protected to ground. Brief short circuits to ground will not degrade reliability, however continuous (100% duty cycle) output current must not exceed 30mA for maximum reliability.

Electrical Specifications V<sub>SUPPLY</sub> = ±5V, A<sub>V</sub> = +1, R<sub>F</sub> = 510Ω, R<sub>L</sub> = 100Ω, Unless Otherwise Specified

		(NOTE 4)		HFA1	405IB (	SOIC)	HFA	1405IP (	PDIP)	
PARAMETER	TEST CONDITIONS	TEST LEVEL	TEMP. (°C)	MIN	TYP	MAX	MIN	ТҮР	MAX	UNITS
INPUT CHARACTERISTICS										
Input Offset Voltage		A	25	-	2	5	-	2	5	mV
		Α	Full		3	8	-	3	8	mV
Average Input Offset Voltage Drift	·	В	Full	-	1	10	•	1	10	μV/°C
Input Offset Voltage	$\Delta V_{CM} = \pm 1.8V$	Α	25	45	48	-	45	48	-	dB
Common-Mode Rejection Ratio	$\Delta V_{CM} = \pm 1.8V$	Α	85	43	46	-	43	46	-	dB
	$\Delta V_{CM} = \pm 1.2V$	Α	-40	43	46	-	43	46	-	dB
Input Offset Voltage	$\Delta V_{PS} = \pm 1.8V$	Α	25	48	52	,	48	52		dB
Power Supply Rejection Ratio	$\Delta V_{PS} = \pm 1.8V$	Α	85	46	48	-	46	48	-	dB
	$\Delta V_{PS} = \pm 1.2V$	Α	-40	46	48	-	46	48		d₿
Non-Inverting Input Bias Current		Α	25	-	6	15	•	6	15	μА
	[	Α	Full		10	25	-	10	25	μΑ
Non-Inverting Input Bias Current Drift		₿	Full	-	5	60	•	5	60	nA/°C
Non-Inverting Input Bias Current	$\Delta V_{PS} = \pm 1.8V$	Α	25	-	0.5	1	-	0.5	1	μA/V
Power Supply Sensitivity	$\Delta V_{PS} = \pm 1.8V$	Α	85	-	0.8	3	-	0.8	3	μAΛV
	$\Delta V_{PS} = \pm 1.2V$	A	-40	•	0.8	3	-	0.8	3	√4ر
Non-Inverting Input Resistance	$\Delta V_{CM} = \pm 1.8V$	Α	25	0.8	1.2	-	0.8	1.2		MΩ
	$\Delta V_{CM} = \pm 1.8V$	Α	85	0.5	0.8	-	0.5	8.0	-	MΩ
	$\Delta V_{CM} = \pm 1.2V$	Α	-40	0.5	8.0	-	0.5	0.8	-	MΩ
Inverting Input Bias Current		Α	25	•	2	7.5	-	2	7.5	μА
		Α	Fuli	•	5	15	-	5	15	μА
Inverting Input Bias Current Drift		В	Full	-	60	200	-	60	200	n <b>A/º</b> C
Inverting Input Bias Current	$\Delta V_{CM} = \pm 1.8V$	Α	25	-	3	6	-	3	6	μ <b>Α</b> /V
Common-Mode Sensitivity	$\Delta V_{CM} = \pm 1.8V$	Α	85	-	4	8	•	4	8	μA/V
	$\Delta V_{CM} = \pm 1.2V$	A	-40	-	4	8	-	4	8	μ <b>Α</b> /V

Inverting Input Bias Current Power Supply Sensitivity  AN	EST CONDITIONS  AVPS = ±1.8V  AVPS = ±1.8V  AVPS = ±1.2V  E = 100kHz  = 100kHz  = 100kHz  AV = -1  AV = -1  AV = -2	TEST LEVEL  A A A C B A A B B B B	TEMP. (°C)  25  85  -40  25  25, 85  -40  25  25, 25  25  25  25	#1.8 ±1.2	TYP  2  4  4  60  1.4  ±2.4  ±1.7  3.5  2.5	5 8 8	#1.8 ±1.2	TYP  2  4  4  60  2.2  ±2.4  ±1.7  3.5  2.5	8 8 - - -	UNITS  μΑ/V  μΑ/V  μΑ/V  Ω  PF  V  V  nV√H  pA√H
Inverting Input Resistance   Input Capacitance   Input Voltage Common Mode   Range (Implied by VIO CMRR, +RIN, and -IBIAS CMS Tests)   Input Noise Voltage Density   f = Non-Inverting Input Noise Current Density   Inverting Input Noise Current Density   TRANSFER CHARACTERISTICS   Copen Loop Transimpedance Gain   AC CHARACTERISTICS (Note 3)   AC CHARACTERISTICS	$AV_{PS} = \pm 1.8V$ $AV_{PS} = \pm 1.2V$ $= 100kHz$ $= 100kHz$ $= 100kHz$ $= 100kHz$ $= 100kHz$ $= 100kHz$	A A C B A A B B C C	85 -40 25 25 25, 85 -40 25 25 25	±1.8 ±1.2	4 4 60 1.4 ±2.4 ±1.7 3.5 2.5	8 8	±1.8 ±1.2	4 4 60 2.2 ±2.4 ±1.7	8 8	μΑ/V μΑ/V Ω pF V V
Inverting Input Resistance  Input Capacitance  Input Voltage Common Mode Range (Implied by V <sub>IO</sub> CMRR, +R <sub>IN</sub> , and -I <sub>BIAS</sub> CMS Tests)  Input Noise Voltage Density  Inverting Input Noise Current Density  Inverting Input Noise Current Density f = TRANSFER CHARACTERISTICS  Open Loop Transimpedance Gain AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  Full Power Barldwidth (V <sub>OUT</sub> = 5V <sub>P-P</sub> , Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  A	= 100kHz = 100kHz = 100kHz = 100kHz = 100kHz	A C B A A B B C C	-40 25 25 25, 85 -40 25 25 25	±1.8 ±1.2	4 60 1.4 ±2.4 ±1.7 3.5 2.5	-	±1.8 ±1.2	4 60 2.2 ±2.4 ±1.7	-	μΑ/V Ω pF V V
Inverting Input Resistance Input Voltage Common Mode Range (Implied by V <sub>IO</sub> CMRR, +R <sub>IN</sub> , and -IBIAS CMS Tests) Input Noise Voltage Density Inverting Input Noise Current Inverting Input Noise Current Inverting Input Noise Current Inverting Input Noise Current Input Noise	= 100kHz = 100kHz = 100kHz = 100kHz	C B A A B B C	25 25 25, 85 -40 25 25 25	±1.8 ±1.2	60 1.4 ±2.4 ±1.7 3.5 2.5	-	±1.8 ±1.2	60 2.2 ±2.4 ±1.7	-	Ω pF V V
Input Capacitance Input Voltage Common Mode Range (Implied by V <sub>IO</sub> CMRR, +R <sub>IN</sub> , and -I <sub>BIAS</sub> CMS Tests) Input Noise Voltage Density Input Noise Voltage Density Inverting Input Noise Current Density Inverting Input Noise Current Density I = TRANSFER CHARACTERISTICS Open Loop Transimpedance Gain AC CHARACTERISTICS (Note 3) -3dB Bandwidth (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  Full Power Barldwidth (V <sub>OUT</sub> = 5V <sub>P-P</sub> , Notes 3, 5)  A Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  A	= 100kHz = 100kHz A <sub>V</sub> = -1	B A A B B C C	25 25, 85 -40 25 25 25	±1.2	1.4 ±2.4 ±1.7 3.5 2.5	-	±1.2	2.2 ±2.4 ±1.7	-	pF V V nV/√F
Input Voltage Common Mode Range (Implied by V <sub>IO</sub> CMRR, +R <sub>IN</sub> , and -I <sub>BIAS</sub> CMS Tests) Input Noise Voltage Density Input Noise Voltage Density Inverting Input Noise Current Inverting Input Noise Input	= 100kHz = 100kHz A <sub>V</sub> = -1	A A B B	25, 85 -40 25 25 25	±1.2	±2.4 ±1.7 3.5 2.5	-	±1.2	±2.4 ±1.7	-	V V IV/√n
Range (Implied by VIO CMRR, +RIN, and -IBIAS CMS Tests)  Input Noise Voltage Density  Input Noise Voltage Density  Inverting Input Noise Current Density  Inverting Input Noise Current Density  Inverting Input Noise Current Density  TRANSFER CHARACTERISTICS  Open Loop Transimpedance Gain  AC CHARACTERISTICS (Note 3)  -3dB Bandwidth  (VOUT = 0.2VP.P, Notes 3, 5)  A  Full Power Barldwidth  (VOUT = 5VP.P, Notes 3, 5)  A  Gain Flatness  (VOUT = 0.2VP.P, Notes 3, 5)  A	= 100kHz = 100kHz A <sub>V</sub> = -1	B B	-40 25 25 25	±1.2	±1.7	-	±1.2	±1.7	-	V nV/√F
(Implied by V <sub>IO</sub> CMRR, +R <sub>IN</sub> , and -I <sub>BIAS</sub> CMS Tests)  Input Noise Voltage Density  Non-Inverting Input Noise Current Density  Inverting Input Noise Current Density f =  TRANSFER CHARACTERISTICS  Open Loop Transimpedance Gain AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  Full Power Barldwidth (V <sub>OUT</sub> = 5V <sub>P-P</sub> , Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  A  A	= 100kHz = 100kHz A <sub>V</sub> = -1	B B	25 25 25		3.5		ļ	3.5	-	nV/√F
Non-Inverting Input Noise Current Density  Inverting Input Noise Current Density f = TRANSFER CHARACTERISTICS  Open Loop Transimpedance Gain A AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (VOUT = 0.2Vp.p, Notes 3, 5)  Full Power Bandwidth (VOUT = 5Vp.p, Notes 3, 5)  A Gain Flatness (VOUT = 0.2Vp.p, Notes 3, 5)  A A	= 100kHz = 100kHz A <sub>V</sub> = -1	В	25 25	-	2.5					<u> </u>
Density  Inverting Input Noise Current Density   f = TRANSFER CHARACTERISTICS  Open Loop Transimpedance Gain   An AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (Vout = 0.2Vp.p, Notes 3, 5)   A AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (Vout = 0.2Vp.p, Notes 3, 5)   A AC CHARACTERISTICS (Note 3)   A AC CHARACTERISTICS (Note 3)   A AC CHARACTERISTICS (Note 3, 5)   A AC CHARACTERISTICS (Note 3)   A AC CHARACTERISTICS (Note 3)   A AC CHARACTERISTICS (Note 3)   A AC CHARACTERISTICS (Note 3, 5)   A AC CHARACTERISTICS (Note 3)   A AC CHARACTERISTICS (Note 3, 5)   A AC CHARACTERISTICS (Note 3)   A AC CHARACTERISTICS (Note 3, 5)   A AC CHARACTERIS	= 100kHz A <sub>V</sub> = -1	В	25	·		-	-	2.5	•	pA/√H
TRANSFER CHARACTERISTICS  Open Loop Transimpedance Gain A:  AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  Full Power Bardwidth (V <sub>OUT</sub> = 5V <sub>P-P</sub> , Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  A	A <sub>V</sub> = -1	С	I		20	-		1		
Open Loop Transimpedance Gain A  AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (VOUT = 0.2Vp.p, Notes 3, 5)  Full Power Bardwidth (VOUT = 5Vp.p, Notes 3, 5)  A  Gain Flatness (VOUT = 0.2Vp.p, Notes 3, 5)  A	A <sub>V</sub> = -1		25				٠ ا	20	-	pA/√F
AC CHARACTERISTICS (Note 3)  -3dB Bandwidth (V <sub>OUT</sub> = 0.2V <sub>P.P</sub> , Notes 3, 5)  A  Full Power Bardwidth (V <sub>OUT</sub> = 5V <sub>P.P</sub> , Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P.P</sub> , Notes 3, 5)  A	A <sub>V</sub> = -1		25							
-3dB Bandwidth (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  A  Full Power Bandwidth (V <sub>OUT</sub> = 5V <sub>P-P</sub> , Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  A	<del></del>	В		- 1	500	•		500	-	kΩ
(V <sub>OUT</sub> = 0.2V <sub>P.P</sub> , Notes 3, 5)  A A Full Power Barldwidth (V <sub>OUT</sub> = 5V <sub>P.P</sub> , Notes 3, 5)  A Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P.P</sub> , Notes 3, 5)  A	<del></del>	В								
Full Power Bandwidth (V <sub>OUT</sub> = 5V <sub>P.P.</sub> Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P.P.</sub> Notes 3, 5)  A	A <sub>V</sub> = +2	-	25	-	420	-	•	360	-	MHz
Full Power Bandwidth (V <sub>OUT</sub> = 5V <sub>P-P</sub> , Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)  A		В	25		560	-	-	400	-	MHz
(V <sub>OUT</sub> = 5V <sub>P.P.</sub> , Notes 3, 5)  A  Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P.P.</sub> , Notes 3, 5)  A	A <sub>V</sub> = +6	В	25	•	140		-	100		MHz
Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P.P.</sub> , Notes 3, 5)	A <sub>V</sub> = -1	В	25	-	260	-	-	260	-	MHz
Gain Flatness (V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)	4 <sub>V</sub> = +2	В	25	•	165	-	-	165	-	MHz
(V <sub>OUT</sub> = 0.2V <sub>P-P</sub> , Notes 3, 5)	A <sub>V</sub> = +6	В	25	-	140	-		100		MHz
<u> </u>	A <sub>V</sub> = -1, To 25MHz	В	25	-	±0.03	-	•	±0.04		dB
A	A <sub>V</sub> = -1, To 50MHz	В	25	•	±0.04	-	-	±0.04	-	ď₿
	A <sub>V</sub> = -1, To 100MHz	В	25	•	-	•	-	±0.06	-	dB
A	$A_V = +2$ , To 25MHz	В	25	-	±0.03	-		±0.04	•	dB
A	A <sub>V</sub> = +2, To 50MHz	В	25	-	±0.03	-		±0.04		dB
A	A <sub>V</sub> = +2, To 100MHz	В	25	-	-	-		±0.06	-	dΒ
A	A <sub>V</sub> = +6, To 15MHz	В	25	·	±0.08	-	·	±0.08	-	dB
Ā	A <sub>V</sub> = +6, To 30MHz	В	25		±0.19	-	-	±0.27	-	dB
Minimum Stable Gain	-	Α	Full	-	1	-		1		V/V
I	5MHz	В	25	-	-60	-	-	-55		dB
(A <sub>V</sub> = +2, All Channels Hostile, Note 5)	10MHz	В	25	-	-56	-	-	-52	-	dΒ
OUTPUT CHARACTERISTICS AV =			e Specifie	d						
Output Voltage Swing A (Note 5)	$A_V = -1$ , $R_L = 100\Omega$	<del></del>	25	±3	±3.4	-	±3	±3.4	<u> </u>	
		Α	Full	±2.8	±3	<u> </u>	±2.8	±3	·	٧
	$A_V = -1$ , $R_L = 50\Omega$	Α	25, 85	50	60	<u> </u>	50	60	<u> </u>	mA
(Note 5)		A	-40	28	42	<u> </u>	28	42	<u> </u>	mA
Output Short Circuit Current		В	25	<u> </u>	90	-	·	90		mA

## Electrical Specifications $V_{SUPPLY} = \pm 5V$ , $A_V = +1$ , $R_F = 510\Omega$ , $R_L = 100\Omega$ , Unless Otherwise Specified (Continued)

		(NOTE 4)		HFA1405IB (SOIC)		HFA1405IP (PDIP)				
PARAMETER	TEST CONDITIONS	TEST LEVEL	TEMP.	MIN	ТҮР	MAX	MiN	TYP	MAX	UNITS
Second Harmonic Distortion	10MHz	В	25	-	-51	-	-	-51		dBc
(V <sub>OUT</sub> = 2V <sub>P-P</sub> , Note 5)	20MHz	В	25	-	-46		·	-46	-	dBc
Third Harmonic Distortion	10MHz	В	25	-	-63		-	-63	-	dBc
$(V_{OUT} = 2V_{P-P}, Note 5)$	20MHz	В	25	-	-56	-	-	-56	-	dBc
TRANSIENT CHARACTERISTICS	A <sub>V</sub> = +2 (Note 3), Ur	less Othen	vise Spe	cified	•			-		
Rise and Fall Times	A <sub>V</sub> = +2	В	25	-	0.8		-	0.9		ns
(V <sub>OUT</sub> = 0.5V <sub>P-P</sub> , Note 3)	A <sub>V</sub> = +6	В	25		2.9			4	- 1	ns
Overshoot	A <sub>V</sub> = -1, +OS	В	25		7	-	_	3	-	%
$(V_{OUT} = 0.5V_{P-P}, V_{IN} t_{RISE} = 1ns,$ Notes 3, 6)	A <sub>V</sub> ≈ -1, -OS	В	25	-	8		-	13	•	%
. 10100 01 01	A <sub>V</sub> = +2, +OS	В	25	-	5	•	-	7		%
	A <sub>V</sub> = +2, -OS	В	25	-	10	-	-	11	- 1	%
	A <sub>V</sub> = +6, +OS	В	25	-	2		-	2	-	%
	A <sub>V</sub> = +6, -OS	В	25		2	•	-	2	-	%
Slew Rate (V <sub>OUT</sub> = 5V <sub>P-P</sub> , Notes 3, 5)	A <sub>V</sub> ≈ -1, +SR	В	25	-	2500	•	-	2500	-	V/μs
	A <sub>V</sub> = -1, -SR	В	25	-	1900		-	1900	-	V/µs
	A <sub>V</sub> = +2, +SR	В	25	-	1700		-	1600	-	V/µs
	A <sub>V</sub> = +2, -SR	В	25	-	1700		-	1400	-	V/µs
	A <sub>V</sub> = +6, +SR	В	25	-	1500	•	-	1000	-	V/μs
	A <sub>V</sub> = +6, -SR	В	25	-	1100	,	-	1000	-	V/µs
Settling Time	To 0.1%	В	25	-	23	,	-	23	-	ns
(V <sub>OUT</sub> = +2V to 0V Step, Note 5)	To 0.05%	В	25	-	30	-	-	30	-	ns
	To 0.025%	В	25	-	37	•	-	40	-	กร
Overdrive Recovery Time	V <sub>IN</sub> = ±2V	В	25	-	8.5	-	-	8.5	-	ns
VIDEO CHARACTERISTICS AV	= +2 (Note 3), Unless	Otherwise	Specified							
Differential Gain	$R_L = 150\Omega$	В	25	-	0.02		-	0.03	- ]	%
(f = 3.58MHz)	$R_L = 75\Omega$	В	25	-	0.03	•	-	0.06	٠	%
Differential Phase	R <sub>L</sub> = 150Ω	8	25	-	0.03			0.03	-	Degree
(f = 3.58MHz)	$R_L = 75\Omega$	В	25		0.06	-	-	0.06	-	Degree
POWER SUPPLY CHARACTERIS	TICS									
Power Supply Range		С	25	±4.5	-	±5.5	±4.5	-	±5.5	V
Power Supply Current (Note 5)		Α	25	-	5.8	6.1	-	5.8	6.1	mA/Op Amp
		А	Full	,	5.9	6.3	-	5.9	6.3	mA/Op Amp

## NOTES:

- The optimum feedback resistor depends on closed loop gain and package type. The following resistors were used for the PDIP/SOIC characterization: A<sub>V</sub> = -1, R<sub>F</sub> = 310Ω/360Ω; A<sub>V</sub> = +2, R<sub>F</sub> = 402Ω/510Ω; A<sub>V</sub> = +6, R<sub>F</sub> = 500Ω/500Ω. See the Application Information section for more information.
- 4. Test Level: A. Production Tested; B. Typical or Guaranteed Limit Based on Characterization; C. Design Typical for Information Only.
- 5. See Typical Performance Curves for more information.
- 6. Undershoot dominates for output signal swings below GND (e.g., 2V<sub>P-P</sub>), yielding a higher overshoot limit compared to the V<sub>OUT</sub> = 0V to 2V condition. See the "Application Information" section for details.

## Application Information

#### Performance Differences Between PDIP and SOIC

The amplifiers comprising the HFA1405 are high frequency current feedback amplifiers. As such, they are sensitive to feedback capacitance which destabilizes the op amp and causes overshoot and peaking. Unfortunately, the standard quad op amp pinout places the amplifier's output next to its inverting input, thus making the package capacitance an unavoidable parasitic feedback capacitor. The larger parasitic capacitance of the PDIP requires an inherently more stable amplifier, which yields a PDIP device with lower performance than the SOIC device - see Electrical Specification tables for details

Because of these performance differences, designers should evaluate and breadboard with the same package style to be used in production.

Note that the "Typical Performance Curves" section has separate pulse and frequency response graphs for each package type. Graphs not labeled with a specific package type are applicable to both packages.

### **Optimum Feedback Resistor**

Although a current feedback amplifier's bandwidth dependency on closed loop gain isn't as severe as that of a voltage feedback amplifier, there can be an appreciable decrease in bandwidth at higher gains. This decrease may be minimized by taking advantage of the current feedback amplifier's unique relationship between bandwidth and Rr. All current feedback amplifiers require a feedback resistor, even for unity gain applications, and RE, in conjunction with the internal compensation capacitor, sets the dominant pole of the frequency response. Thus, the amplifier's bandwidth is inversely proportional to RF. The HFA1405 design is optimized for  $R_F \approx 402\Omega/510\Omega$  (PDIP/SOIC) at a gain of +2. Decreasing Re decreases stability, resulting in excessive peaking and overshoot (Note: Capacitive feedback causes the same problems due to the feedback impedance decrease at higher frequencies). However, at higher gains the amplifier is more stable so RF can be decreased in a trade-off of stability for bandwidth.

The table below lists recommended R<sub>F</sub> values for various gains, and the expected bandwidth. For good channel-to-channel gain matching, it is recommended that all resistors (termination as well as gain setting) be  $\pm 1\%$  tolerance or better.

#### **OPTIMUM FEEDBACK RESISTOR**

GAIN (A <sub>CL</sub> )	R <sub>F</sub> (Ω) PDIP/SOIC	BANDWIDTH (MHz) PDIP/SOIC
-1	310/360	360/420
+2	402/510	400/560
+6	500/500 (Note)	100/140

NOTE:  $R_F = 500\Omega$  is not the optimum value. It was chosen to match the  $R_F$  of the CLC414 and CLC415, for performance comparison purposes. Performance at  $A_V = +6$  may be increased by reducing  $R_F$  below  $500\Omega$ 

## Non-inverting Input Source Impedance

For best operation, the DC source impedance seen by the non-inverting input should be  $\geq 50\Omega$ . This is especially important in inverting gain configurations where the non-inverting input would normally be connected directly to GND.

#### Pulse Undershoot

The HFA1405 utilizes a quasi-complementary output stage to achieve high output current while minimizing quiescent supply current. In this approach, a composite device replaces the traditional PNP pulldown transistor. The composite device switches modes after crossing 0V, resulting in added distortion for signals swinging below ground, and an increased undershoot on the negative portion of the output waveform (see Figure 6 and Figure 9). This undershoot isn't present for small bipolar signals, or large positive signals (see Figure 5 and Figure 8).

## PC Board Lavout

The frequency response of this amplifier depends greatly on the amount of care taken in designing the PC board. The use of low inductance components such as chip resistors and chip capacitors is strongly recommended, while a solid ground plane is a must!

Attention should be given to decoupling the power supplies. A large value  $(10\mu F)$  tantalum in parallel with a small value  $(0.1\mu F)$  chip capacitor works well in most cases.

Terminated microstrip signal lines are recommended at the input and output of the device. Capacitance, parasitic or planned, connected to the output must be minimized, or isolated as discussed in the next section.

Care must also be taken to minimize the capacitance to ground seen by the amplifier's inverting input (-IN). The larger this capacitance, the worse the gain peaking, resulting in pulse overshoot and eventual instability. To reduce this capacitance the designer should remove the ground plane under traces connected to -IN, and keep connections to -IN as short as possible.

An example of a good high frequency layout is the Evaluation Board shown in Figure 3.

## **Driving Capacitive Loads**

Capacitive loads, such as an A/D input, or an improperty terminated transmission line will degrade the amplifier's phase margin resulting in frequency response peaking and possible oscillations. In most cases, the oscillation can be avoided by placing a resistor (R<sub>S</sub>) in series with the output prior to the capacitance.

Figure 1 details starting points for the selection of this resistor. The points on the curve indicate the R<sub>S</sub> and C<sub>L</sub> combinations for the optimum bandwidth, stability, and settling time, but experimental fine tuning is recommended. Picking a point above or to the right of the curve yields an overdamped response, while points below or left of the curve indicate areas of underdamped performance.

 $\rm R_S$  and  $\rm C_L$  form a low pass network at the output, thus limiting system bandwidth well below the amplifier bandwidth of 560MHz. By decreasing  $\rm R_S$  as  $\rm C_L$  increases (as illustrated in the curve), the maximum bandwidth is obtained without sacrificing stability. In spite of this, bandwidth still decreases as the load capacitance increases.

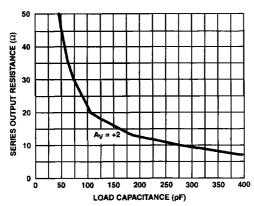


FIGURE 1. RECOMMENDED SERIES OUTPUT RESISTOR VS LOAD CAPACITANCE

## **Evaluation Board**

The performance of the HFA1405 (PDIP) may be evaluated using the HA5025 Evaluation Board.

The schematic for amplifier 1 and the board layout are shown in Figure 2 and Figure 3. Resistors  $R_{\text{F}}$  and  $R_{\text{G}}$  may require a change to values applicable to the HFA1405.

To order evaluation boards (part number HA5025EVAL), please contact your local sales office.

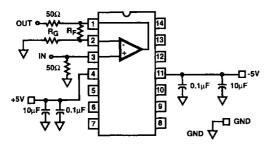
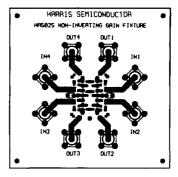


FIGURE 2. EVALUATION BOARD SCHEMATIC

#### TOP LAYOUT



#### **BOTTOM LAYOUT**

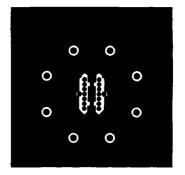
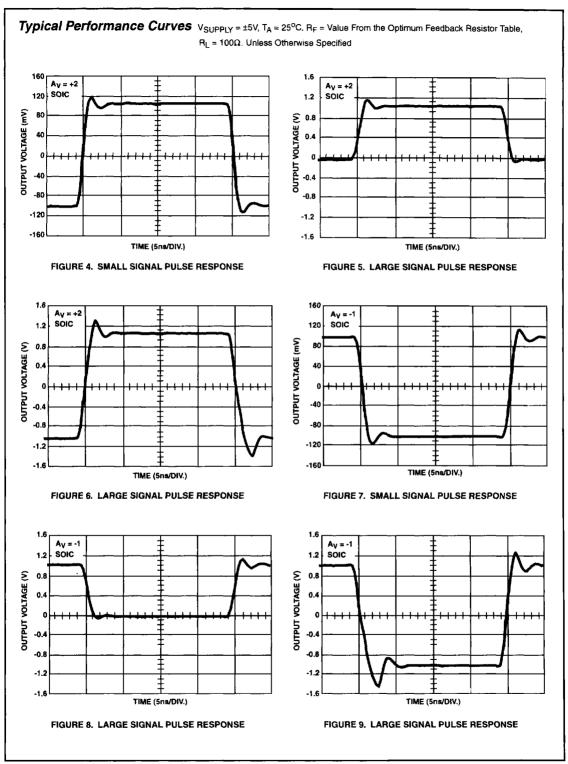
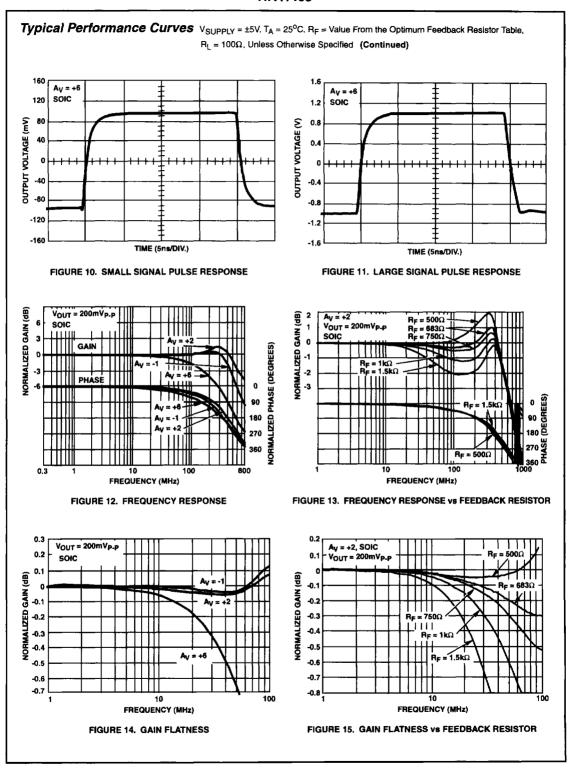
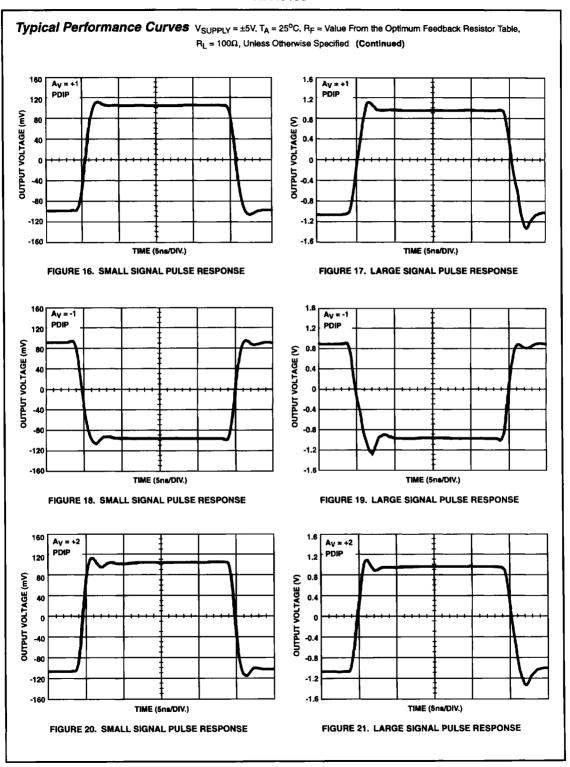
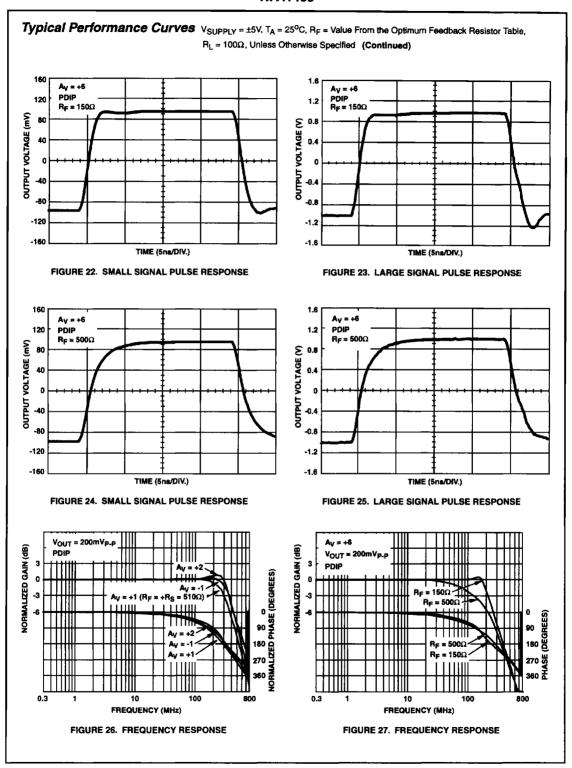


FIGURE 3. EVALUATION BOARD LAYOUT

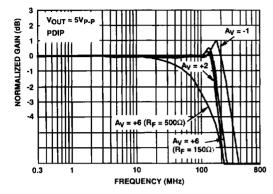








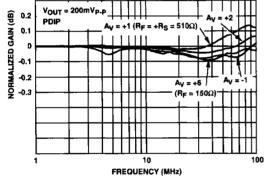
**Typical Performance Curves**  $V_{SUPPLY} = \pm 5V$ ,  $T_A = 25^{\circ}C$ ,  $R_F = Value$  From the Optimum Feedback Resistor Table,  $R_1 = 100\Omega$ , Unless Otherwise Specified (Continued)



 $\widehat{\mathbf{g}}$  2  $\mathbf{A_V} = +2$   $\mathbf{V_{OUT}} = 200 \text{mV}_{P.P}$   $\mathbf{R_F} = 365\Omega$   $\mathbf{R_F} = 365\Omega$   $\mathbf{PDIP}$   $\mathbf{R_F} = 365\Omega$   $\mathbf{R_F} =$ 

FIGURE 28. FULL POWER BANDWIDTH

FIGURE 29. FREQUENCY RESPONSE vs FEEDBACK RESISTOR



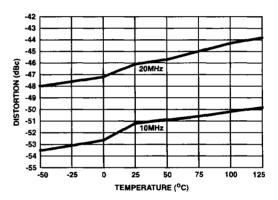
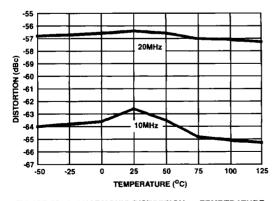


FIGURE 30. GAIN FLATNESS

FIGURE 31. 2nd HARMONIC DISTORTION vs TEMPERATURE



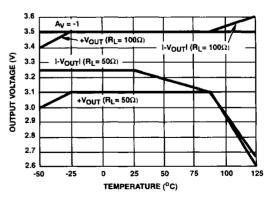
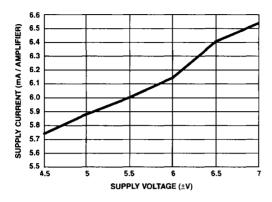


FIGURE 32. 3rd HARMONIC DISTORTION vs TEMPERATURE

FIGURE 33. OUTPUT VOLTAGE vs TEMPERATURE

**Typical Performance Curves**  $V_{SUPPLY} = \pm 5V$ ,  $T_A = 25^{\circ}C$ ,  $R_F = Value$  From the Optimum Feedback Resistor Table,  $R_L = 100\Omega$ , Unless Otherwise Specified (**Continued**)



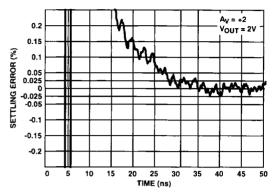
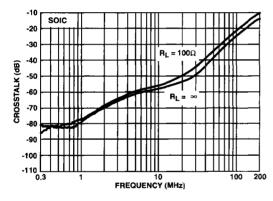


FIGURE 34. SUPPLY CURRENT vs SUPPLY VOLTAGE

FIGURE 35. SETTLING RESPONSE



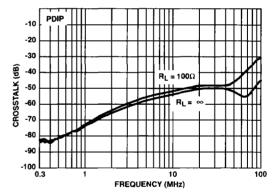


FIGURE 36. ALL HOSTILE CROSSTALK

FIGURE 37. ALL HOSTILE CROSSTALK

## Die Characteristics

#### **DIE DIMENSIONS:**

79 mils x 118 mils x 19 mils 2000μm x 3000μm x 483μm

#### **METALLIZATION:**

Type: Metal 1: AlCu(2%)/TiW Thickness: Metal 1: 8kÅ ±0.4kÅ

Type: Metal 2: AlCu(2%)

Thickness: Metal 2: 16kÅ ±0.8kÅ

## SUBSTRATE POTENTIAL (Powered Up):

Floating (Recommend Connection to V-)

## PASSIVATION:

Type: Nitride

Thickness: 4kA ±0.5kA

## TRANSISTOR COUNT:

320

## Metallization Mask Layout

#### HFA1405

